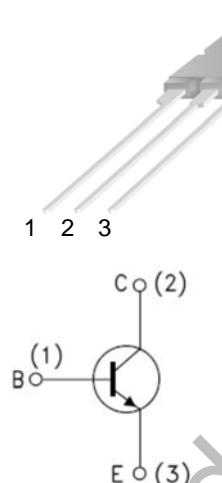


 WGC5453	 TO-264	
Features: <ul style="list-style-type: none"> <input type="checkbox"/> High Switching Speed <input type="checkbox"/> High Breakdown Voltage-V(BR)CBO= 1200V(Min) <input type="checkbox"/> Minimum Lot-to-Lot variations for robust device performance and reliable operation 	 1. Base (B) 2. Collector (C) 3. Emitter (E)	

Absolute Maximum Ratings $T_C=25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Rating	Units
V_{CBO}	Collector-Base Voltage	1200	V
V_{CEO}	Collector-Emitter Voltage	800	V
V_{EBO}	Emitter-Base Voltage	6	V
I_C	Collector Current (DC)	25	A
I_{CP}^*	Collector Current (Pulse)	30	A
P_C	Collector Dissipation	200	W
T_J	Junction Temperature	150	$^\circ\text{C}$
T_{STG}	Storage Temperature	-55 ~ 150	$^\circ\text{C}$

* Pulse Test: PW=300 μs , duty Cycle=2% Pulsed

Electrical Characteristics $T_C=25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
I_{CES}	Collector Cut-off Current	$V_{CB}=1400\text{V}$, $R_{BE}=0$			1	mA
I_{CBO}	Collector Cut-off Current	$V_{CB}=800\text{V}$, $I_E=0$			10	μA
I_{EBO}	Emitter Cut-off Current	$V_{EB}=4\text{V}$, $I_C=0$			1	mA
BV_{CBO}	Collector-Base Breakdown Voltage	$I_C=500\mu\text{A}$, $I_E=0$	1200			V
BV_{CEO}	Collector-Emitter Breakdown Voltage	$I_C=5\text{mA}$, $I_B=0$	800			V
BV_{EBO}	Emitter-Base Breakdown Voltage	$I_E=500\mu\text{A}$, $I_C=0$	6			V
h_{FE1} h_{FE2}	DC Current Gain	$V_{CE}=5\text{V}$, $I_C=1\text{A}$ $V_{CE}=5\text{V}$, $I_C=11\text{A}$	8 5.5		8.5	
$V_{CE(\text{sat})}$	Collector-Emitter Saturation Voltage	$I_C=11\text{A}$, $I_B=2.75\text{A}$			3	V
$V_{BE(\text{sat})}$	Base-Emitter Saturation Voltage	$I_C=11\text{A}$, $I_B=2.75\text{A}$			1.5	V
t_{STG}^*	Storage Time	$V_{CC}=200\text{V}$, $I_C=10\text{A}$, $R_L=20\Omega$ $I_{B1}=2.0\text{A}$, $I_{B2}=-4.0\text{A}$			3	μs
t_F^*	Fall Time			0.15	0.2	μs

* Pulse Test: PW=20 μs , duty Cycle=1% Pulsed

Thermal Characteristics $T_C=25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Typ	Max	Units
$R_{\theta jC}$	Thermal Resistance, Junction to Case		0.625	$^\circ\text{C}/\text{W}$

Typical Characteristics

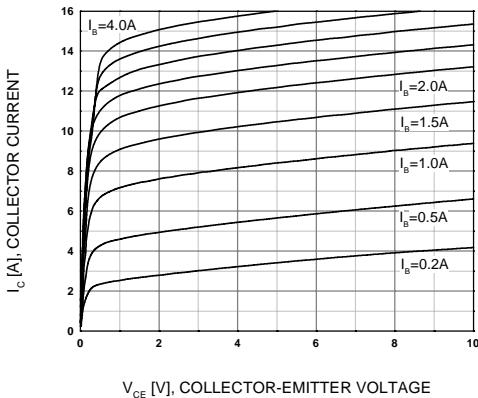


Figure 1. Static Characteristics

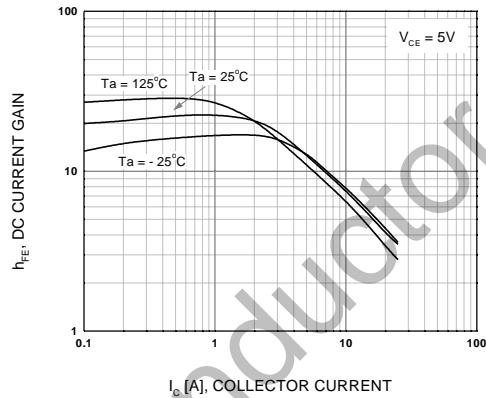


Figure 2. DC Current Gain

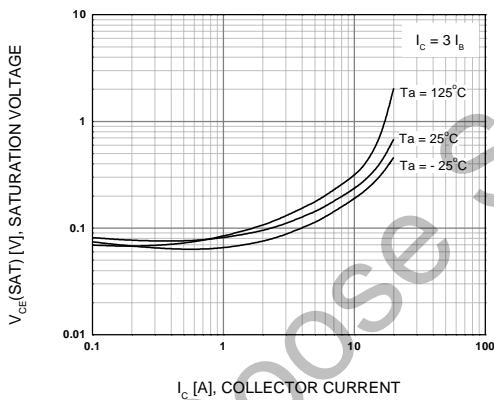


Figure 3. Collector-Emitter Saturation Voltage

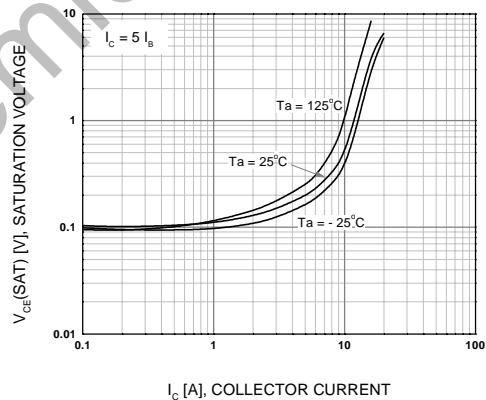


Figure 4. Collector-Emitter Saturation Voltage

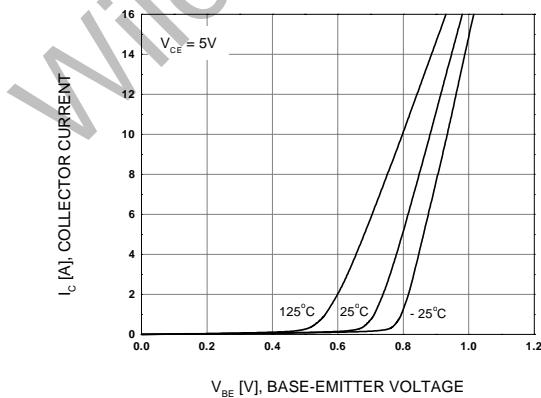


Figure 5. Base-Emitter On Voltage

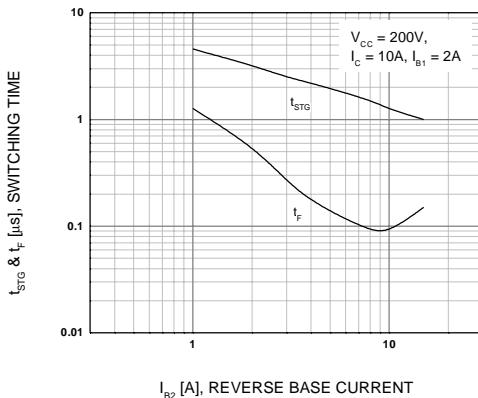


Figure 6. Resistive Load Switching Time

Typical Characteristics (Continued)

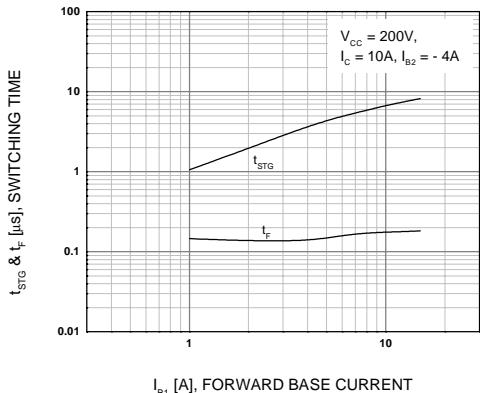


Figure 7. Resistive Load Switching Time

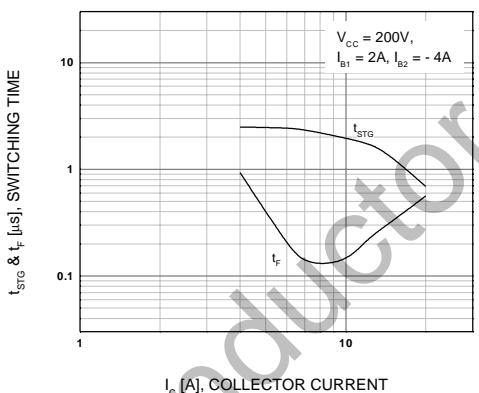


Figure 8. Resistive Load Switching Time

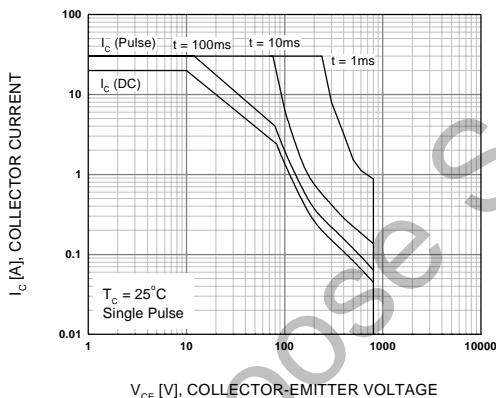


Figure 9. Forward Bias Safe Operating Area

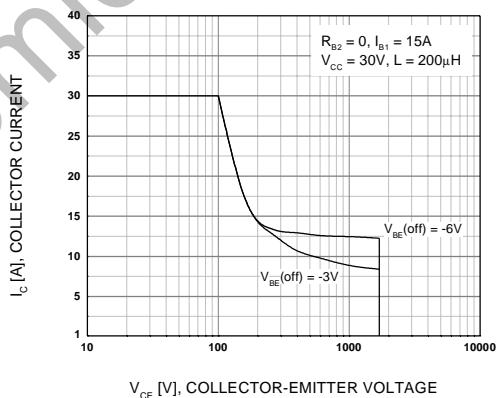


Figure 10. Reverse Bias Safe Operating Area

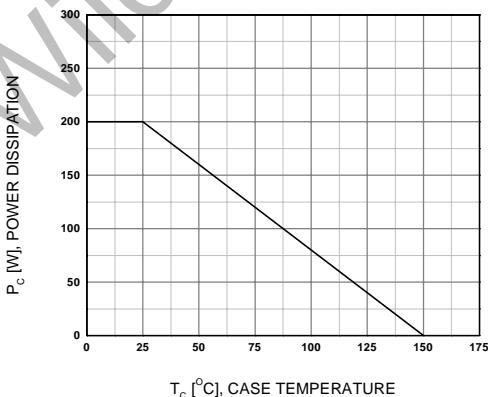
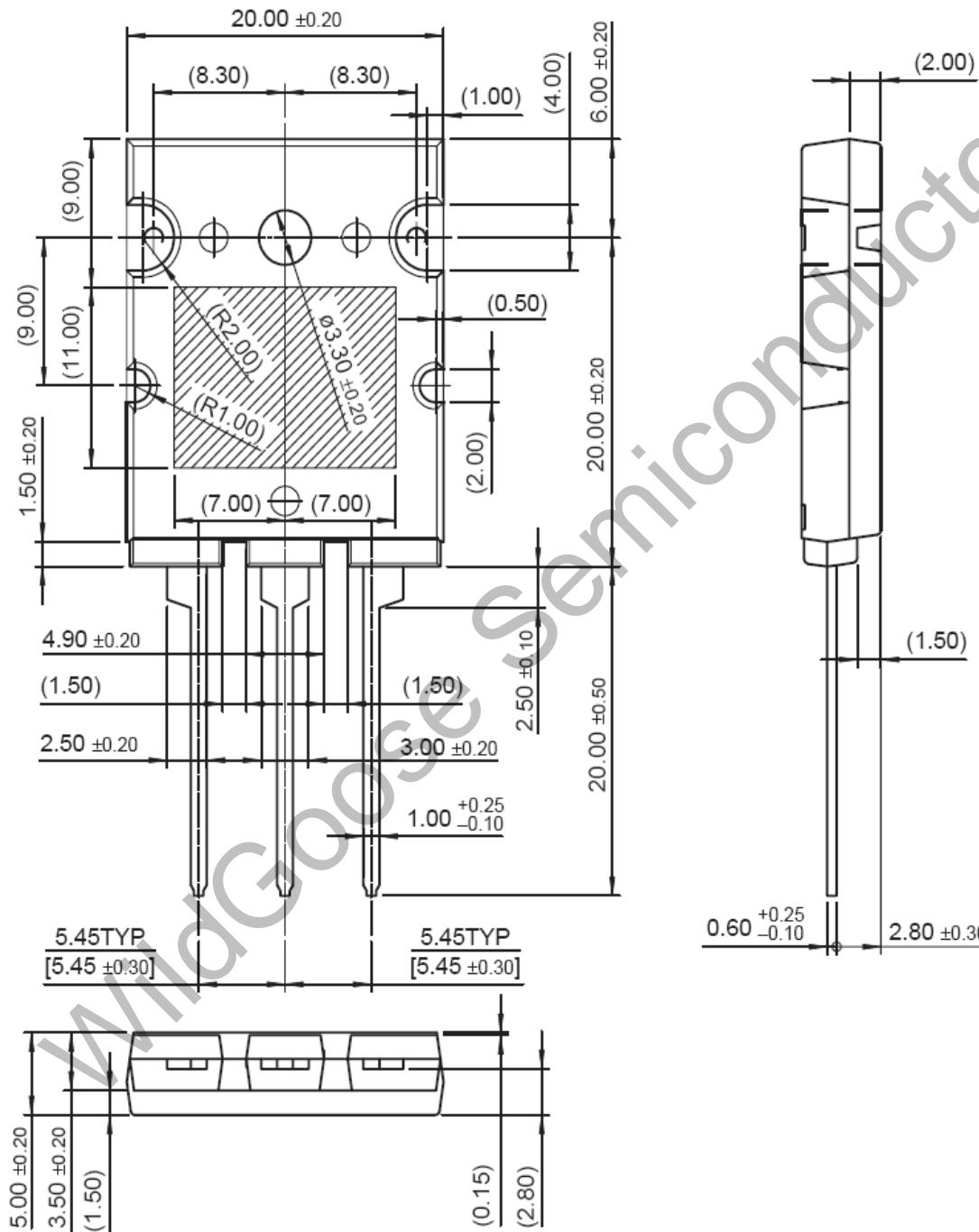


Figure 11. Power Derating

Package Dimension

TO-264

Unit: mm



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